

WHAT IS CLAIMED IS:

1. A solid-state image pickup device having:

unit pixels arranged in a matrix form, each pixel unit comprising a photoelectrical conversion element, a transfer transistor for transferring a signal of said photoelectrical conversion element to a floating node, an amplifying transistor for outputting a signal of said floating node to a signal line, a reset transistor for resetting said floating node, and a P-type MOS transistor, wherein said P-type MOS transistor is connected between a wire to which a main electrode of said reset transistor at the opposite side to said floating node is connected and a driving circuit for selectively applying a reset voltage to said wire.

2. The solid-state image pickup device as claimed in claim 1, wherein the channel voltage of said P-type MOS transistor is equal to 0.4V to 0.7V.

3. A camera system comprising:

a solid-state image pickup device in which a unit pixel has a photoelectrical conversion element, a transfer transistor for transferring a signal of said photoelectrical conversion element to a floating node, an amplifying transistor for outputting a signal of said floating node to a signal line, a reset transistor for resetting said floating node, a P-type MOS transistor, an optical system for guiding incident light to said image pickup portion of said solid-state image pickup

device; and a signal processing circuit for processing the output signal of said solid-state image pickup device, wherein said P-type MOS transistor, is connected between a wire to which a main electrode of said reset transistor at the opposite side to said floating node is connected and a driving circuit for selectively applying a reset voltage to said wire.